



## UTG75N65-S

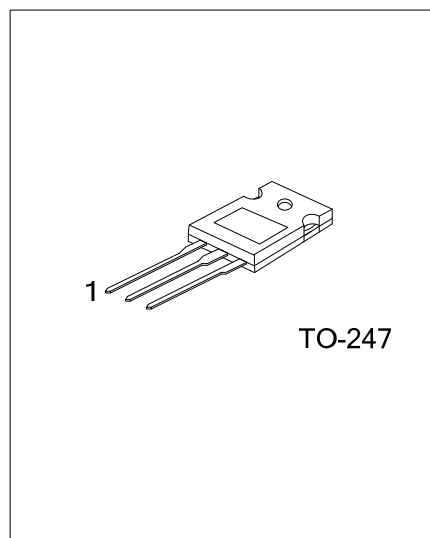
*Insulated Gate Bipolar Transistor*

### 650V TRENCH GATE FIELD-STOP IGBT

#### DESCRIPTION

The UTC **UTG75N65-S** is an Trench Field-Stop Insulated Gate Bipolar Transistor. it uses UTC's advanced technology to provide customers with high switching speed, low saturation voltage and low switching loss, etc.

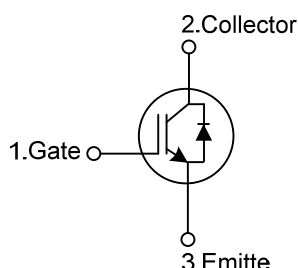
The UTC **UTG75N65-S** is suitable for the resonant or soft switching applications.



#### FEATURES

- \* High switching speed
- \* High avalanche ruggedness
- \* Low saturation voltage:  $V_{CE(SAT), Typ.} = 1.65V @ I_C = 75A, V_{GE} = 15V$  ( $T_C = 25^\circ C$ )

#### SYMBOL



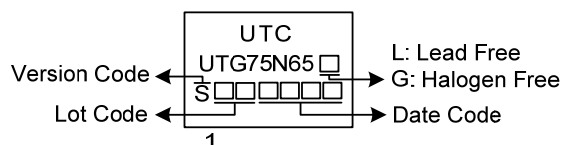
#### ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UTG75N65L-S-T47-T	UTG75N65G-S-T47-T	TO-247	G	C	E	Tube

Note: Pin Assignment: G: Gate C: Collector E: Emitter

<p>UTG75N65G-S-T47-T</p> <p>(1)Packing Type (2)Package Type (3) Version Code (4)Green Package</p>		(1) T: Tube (2) T47: TO-247 (3) Version S (4) G: Halogen Free and Lead Free, L: Lead Free
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#### MARKING



■ ABSOLUTE MAXIMUM RATINGS ( $T_A=25^{\circ}\text{C}$ , unless otherwise noted)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Emitter Voltage	$V_{CES}$	650	V
Gate-Emitter Voltage	$V_{GES}$	$\pm 20$	V
Transient Gate-emitter voltage ( $t_p < 5 \text{ ms}$ )		$\pm 25$	V
Continuous Collector Current	$I_C$	$T_C=25^{\circ}\text{C}$	A
		$T_C=100^{\circ}\text{C}$	A
Collector Current Pulsed (Note 1)	$I_{CM}$	300	A
Diode Forward Current	$I_F$	$T_C=25^{\circ}\text{C}$	A
		$T_C=100^{\circ}\text{C}$	A
Short Circuit Withstand Time $V_{GE} = 15\text{V}$ , $V_{CC} \leq 200\text{V}$ Allowed number of short circuits $< 1000$ Time between short circuits: $\geq 1.0\text{s}$ $T_{VJ} = 25^{\circ}\text{C}$	$t_{SC}$	3	$\mu\text{s}$
Power Dissipation ( $T_C=25^{\circ}\text{C}$ )	$P_D$	310	W
Operating Junction Temperature	$T_J$	$-40 \sim +150$	$^{\circ}\text{C}$
Storage Temperature Range	$T_{STG}$	$-55 \sim +150$	$^{\circ}\text{C}$

Notes: 1. Absolute maximum ratings are stress ratings only and functional device operation is not implied.  
Absolute maximum ratings are those values beyond which the device could be permanently damaged.  
2. Pulse width limited by maximum junction temperature.

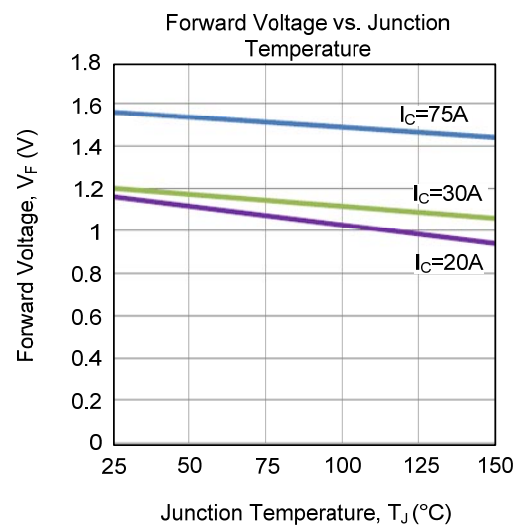
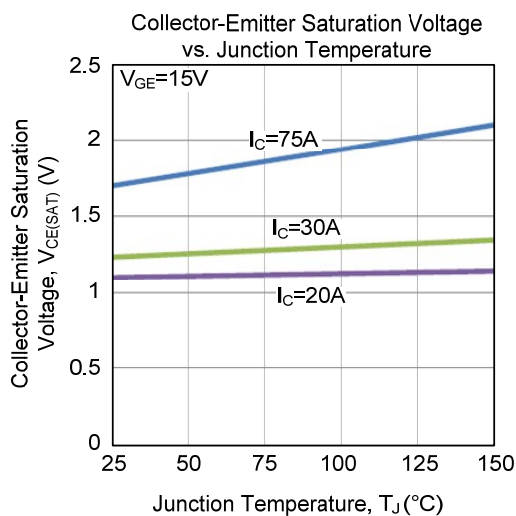
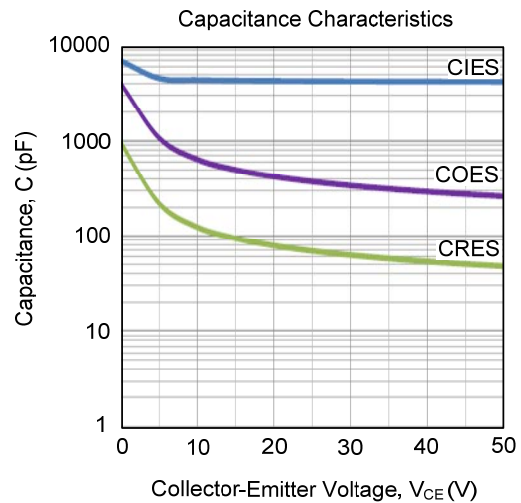
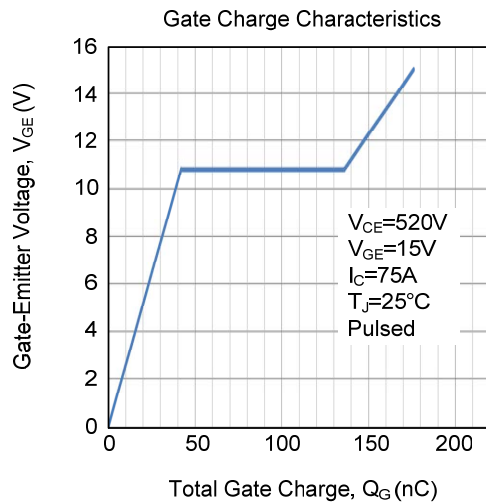
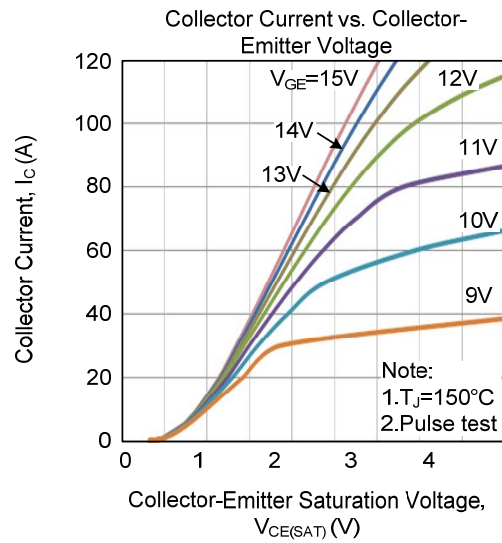
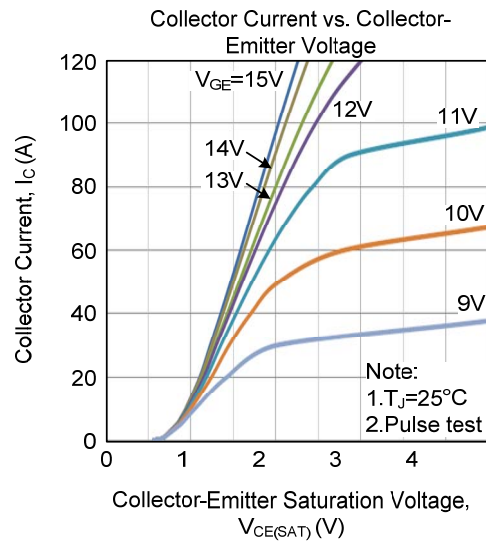
■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Case	$\theta_{JC}$	0.4	$^{\circ}\text{C/W}$

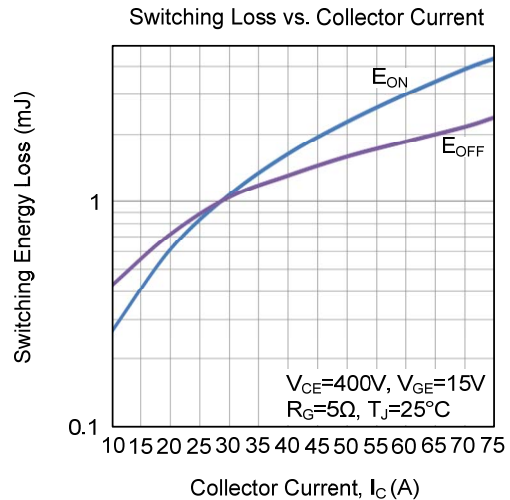
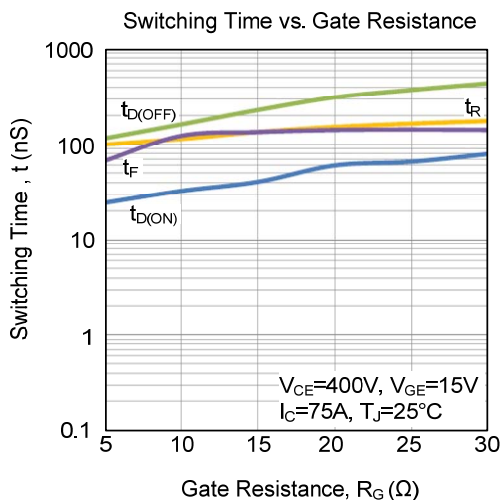
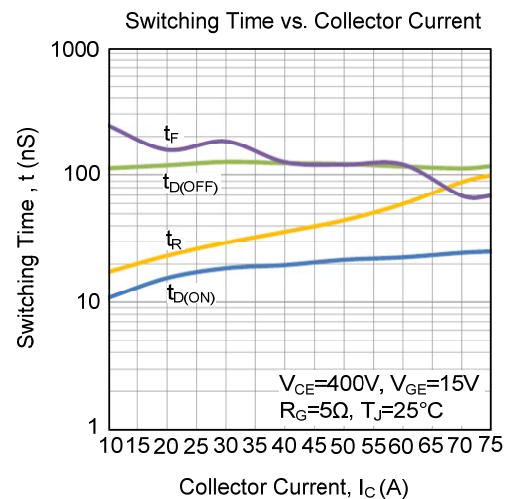
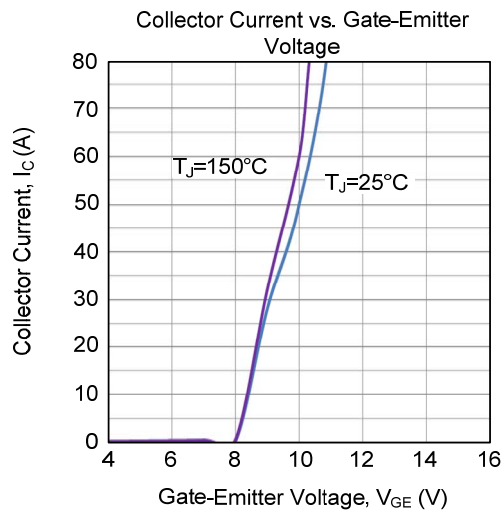
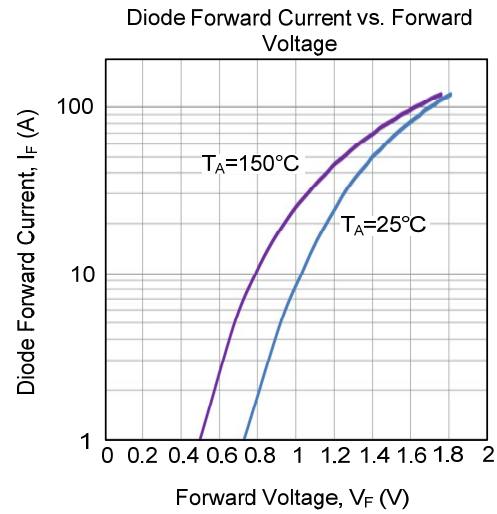
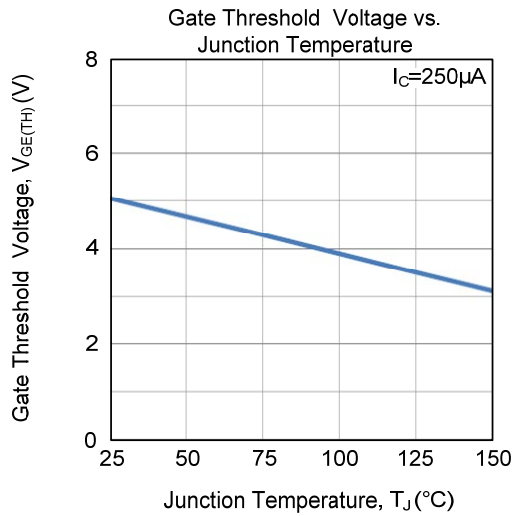
■ ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Off Characteristics						
Collector-Emitter Breakdown Voltage	BV <sub>CES</sub>		650			V
Collector Cut-Off Current	I <sub>CES</sub>	V <sub>CE</sub> =650V, V <sub>GE</sub> =0V			5	μA
G-E Leakage Current	I <sub>GES</sub>	V <sub>CE</sub> =0V, V <sub>GE</sub> =±20V			±400	nA
On Characteristics						
Gate to Emitter Threshold Voltage	V <sub>GE(TH)</sub>	I <sub>C</sub> =250μA, V <sub>CE</sub> =V <sub>GE</sub>	4.5		6.5	V
Collector to Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	I <sub>C</sub> =75A, V <sub>GE</sub> =15V	T <sub>C</sub> =25°C	1.65	2.1	V
			T <sub>C</sub> =125°C	2.0		V
Dynamic Characteristics						
Input Capacitance	C <sub>IES</sub>	V <sub>CE</sub> =25V, V <sub>GE</sub> =0V, f=1MHz		4240		pF
Output Capacitance	C <sub>OES</sub>			370		pF
Reverse Transfer Capacitance	C <sub>RES</sub>			70		pF
Switching Characteristics						
Total Gate Charge	Q <sub>G</sub>	V <sub>CE</sub> =520V, I <sub>C</sub> =75A, V <sub>GE</sub> =15V		180		nC
Gate-Emitter Charge	Q <sub>GE</sub>			41		nC
Gate-Collector Charge	Q <sub>GC</sub>			97		nC
Turn-On Delay Time	t <sub>DON</sub>	V <sub>CC</sub> =400V, I <sub>C</sub> =75A, R <sub>G</sub> =5Ω, V <sub>GE</sub> =0~15V, L=100μH		25		ns
Rise Time	t <sub>R</sub>			100		ns
Turn-Off Delay Time	t <sub>DOFF</sub>			125		ns
Fall Time	t <sub>F</sub>			65		ns
Turn-On Switching Loss	E <sub>ON</sub>			4.27		mJ
Turn-Off Switching Loss	E <sub>OFF</sub>			2.37		mJ
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Forward Voltage Drop	V <sub>F</sub>	I <sub>F</sub> =75A		1.6	2.0	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =75A, dI/dt=100A/μS, V <sub>CC</sub> =400V		52		ns
Reverse Recovery Charge	Q <sub>rr</sub>			629		nC

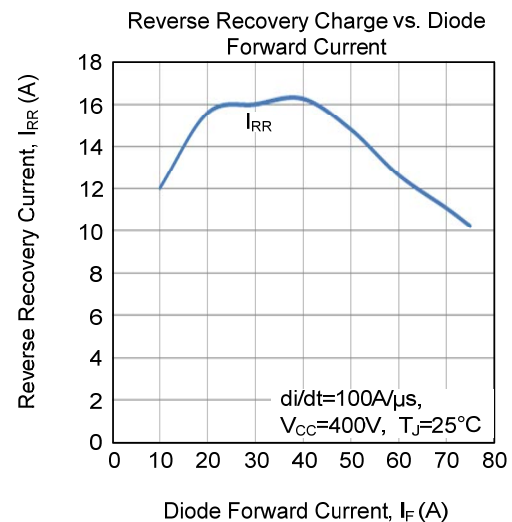
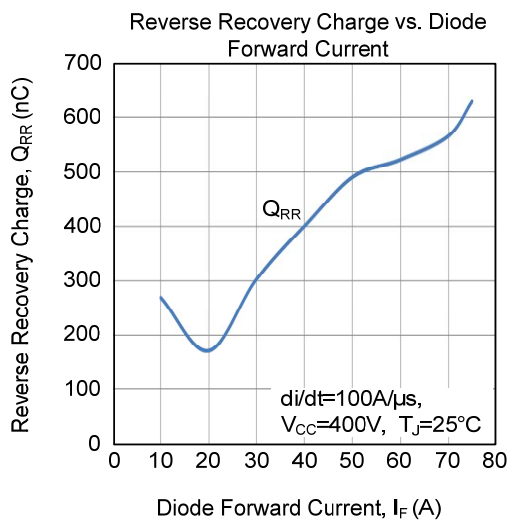
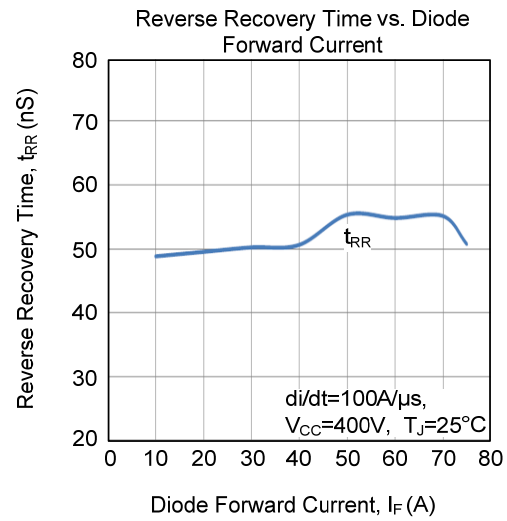
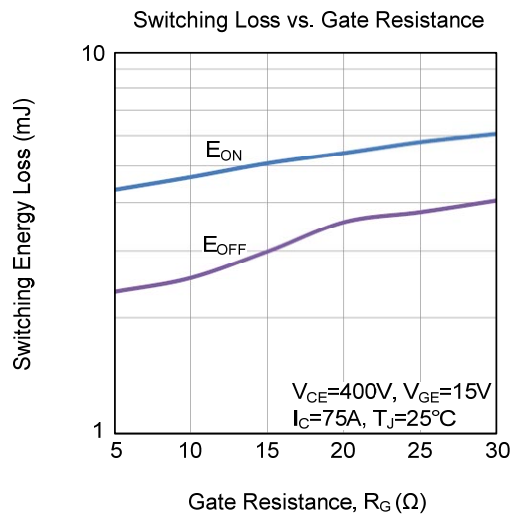
### ■ TYPICAL CHARACTERISTICS



### ■ TYPICAL CHARACTERISTICS (Cont.)



### ■ TYPICAL CHARACTERISTICS (Cont.)



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